
VLSI TECHNOLOGY

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CONTENTS

List of Contributors	xi
Preface	xiii
Introduction	1
Chapter 1 Crystal Growth and Wafer Preparation	9
C. W. Pearce	
1.1 Introduction	9
1.2 Electronic-Grade Silicon	10
1.3 Czochralski Crystal Growing	14
1.4 Silicon Shaping	32
1.5 Processing Considerations	42
1.6 Summary and Future Trends	46
References	47
Problems	49
Chapter 2 Epitaxy	51
C. W. Pearce	
2.1 Introduction	51
2.2 Vapor-Phase Epitaxy	52
2.3 Molecular Beam Epitaxy	74
2.4 Silicon on Insulators	80
2.5 Epitaxial Evaluation	85
2.6 Summary and Future Trends	88
References	88
Problems	92
	v

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Chapter 3	Dielectric and Polysilicon Film Deposition	93
	A. C. Adams	
3.1	Introduction	93
3.2	Deposition Processes	94
3.3	Polysilicon	99
3.4	Silicon Dioxide	106
3.5	Silicon Nitride	119
3.6	Plasma-Assisted Depositions	120
3.7	Other Materials	124
3.8	Summary and Future Trends	125
	References	126
	Problems	128
Chapter 4	Oxidation	131
	L. E. Katz	
4.1	Introduction	131
4.2	Growth Mechanism and Kinetics	132
4.3	Oxidation Techniques and Systems	149
4.4	Oxide Properties	153
4.5	Redistribution of Dopants at Interface	157
4.6	Oxidation of Polysilicon	159
4.7	Oxidation-Induced Defects	160
4.8	Summary and Future Trends	164
	References	165
	Problems	167
Chapter 5	Diffusion	169
	J. C. C. Tsai	
5.1	Introduction	169
5.2	Models of Diffusion in Solids	170
5.3	Fick's One-Dimensional Diffusion Equations	172
5.4	Atomistic Diffusion Mechanisms	177
5.5	Measurement Techniques	184
5.6	Diffusivities of B, P, As, and Sb	193
5.7	Diffusion in SiO ₂	204
5.8	Fast Diffusants in Silicon	206
5.9	Diffusion in Polycrystalline Silicon	207
5.10	Diffusion Enhancements and Retardations	209
5.11	Summary and Future Trends	214
	References	215
	Problems	217

Chapter 6	Ion Implantation	219
	T. E. Seidel	
6.1	Introduction	219
6.2	Ion Implant System and Dose Control	220
6.3	Ion Ranges	224
6.4	Disorder Production	235
6.5	Annealing of Implanted Dopant Impurities	242
6.6	Shallow Junctions (As, BF ₂)	253
6.7	Minority-Carrier Effects	255
6.8	Gettering	255
6.9	Effects in VLSI Processing	258
6.10	Summary and Future Trends	260
	References	261
	Problems	264
Chapter 7	Lithography	267
	D. A. McGillis	
7.1	Introduction	267
7.2	The Lithographic Process	268
7.3	Optical Lithography	274
7.4	Electron Beam Lithography	281
7.5	X-Ray Lithography	287
7.6	Other Lithography Techniques	294
7.7	Summary and Future Trends	298
	References	299
	Problems	300
Chapter 8	Dry Etching	303
	C. J. Mogab	
8.1	Introduction	303
8.2	Pattern Transfer	304
8.3	Low-Pressure Gas Discharges	312
8.4	Plasma-Assisted Etching Techniques	317
8.5	Control of Etch Rate and Selectivity	321
8.6	Control of Edge Profile	330
8.7	Side Effects	334
8.8	Dry Etching Processes for VLSI Technology	336
8.9	Summary of Future Trends	341
	References	342
	Problems	344

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